



YJQ70G06A

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS}				



Typical Electrical and Thermal Characteristics Diagrams

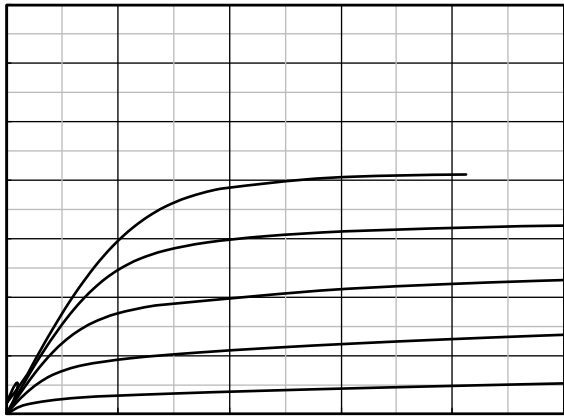


Figure 1. Output Characteristics

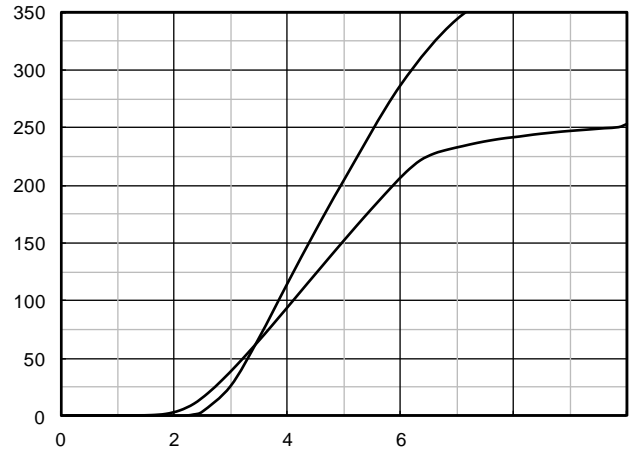


Figure 2. Transfer Characteristics

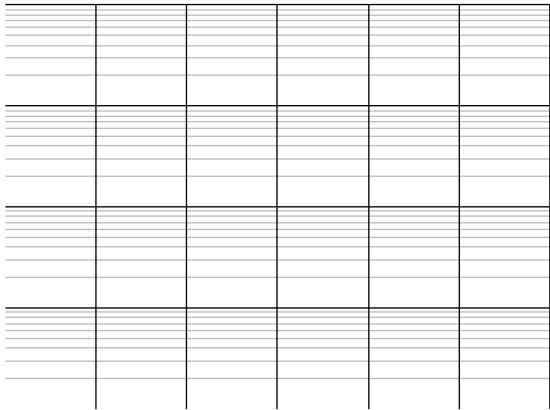


Figure 3. Capacitance Characteristics

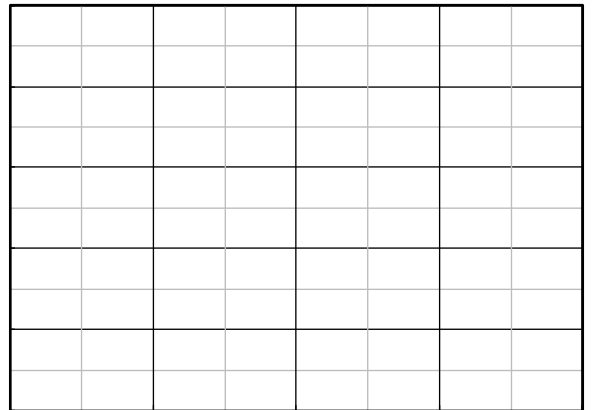


Figure 4. Gate Charge

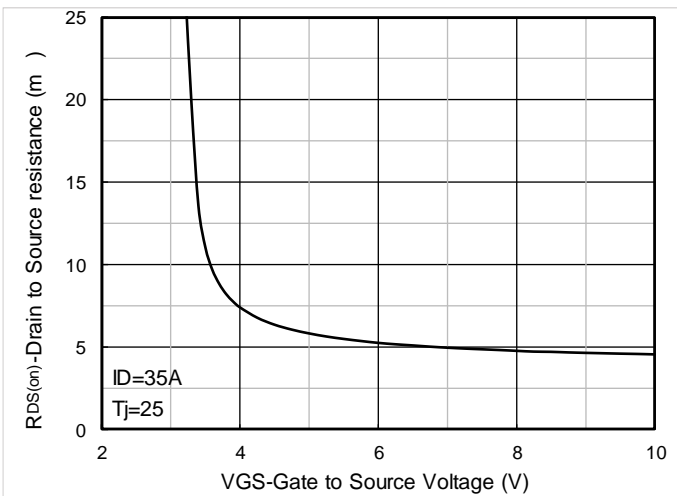
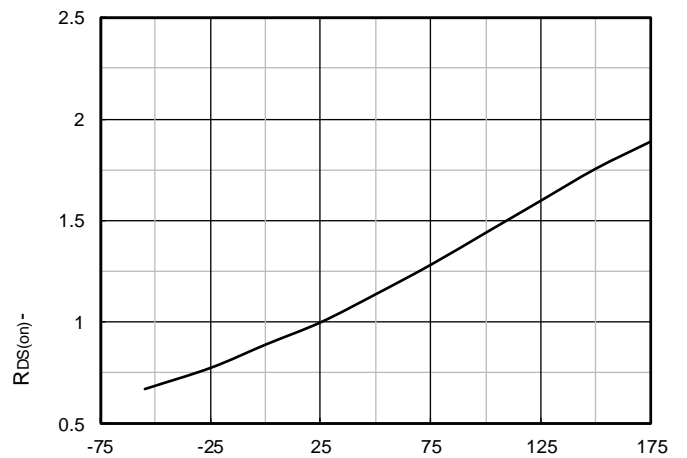


Figure 5.



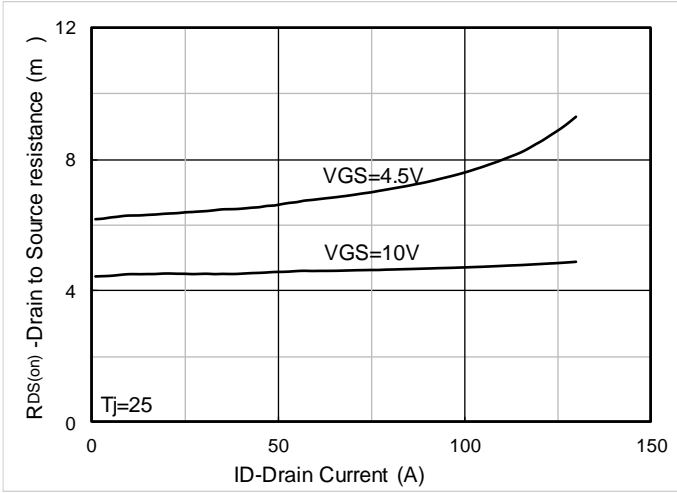


Figure 7. $R_{DS(on)}$ VS Drain Current

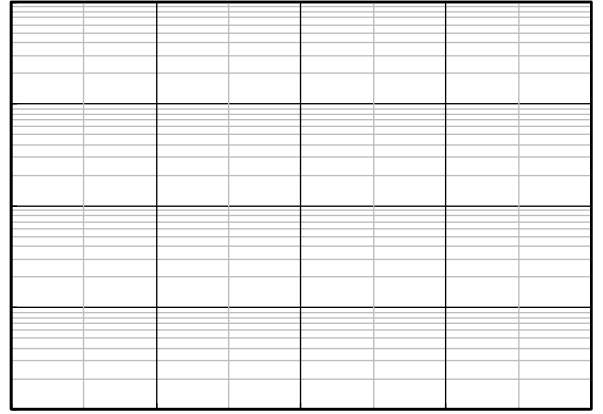


Figure 8. Forward characteristics of reverse diode

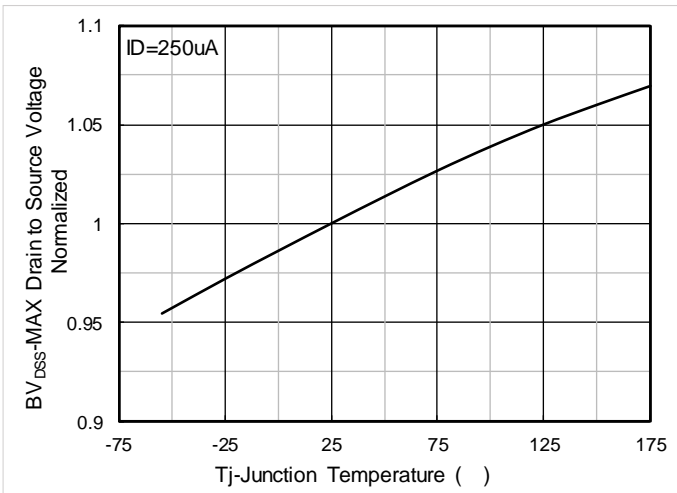
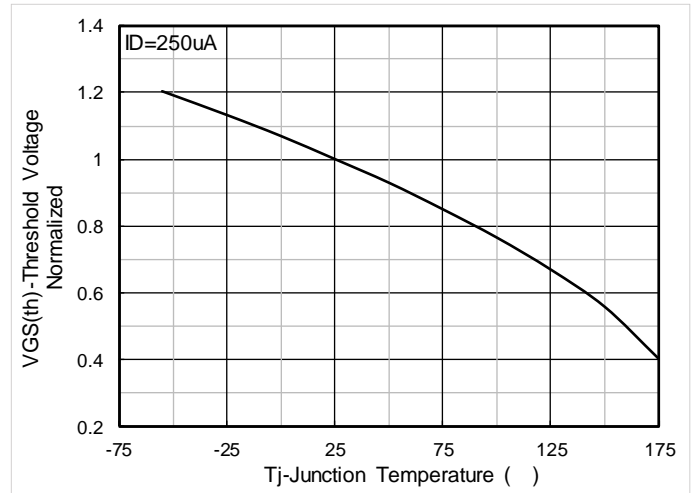


Figure 9. Normalized breakdown v8821Q EMC /P \AA CID 4/Lang (en6 355ag0008882 0 596.04 842.04 reW* nBT/F5 9



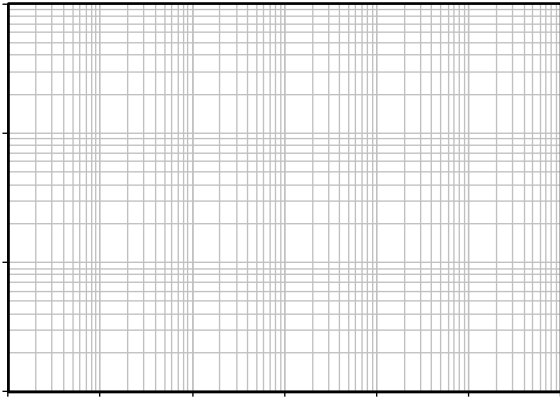


Figure 13. Maximum Transient Thermal Impedance

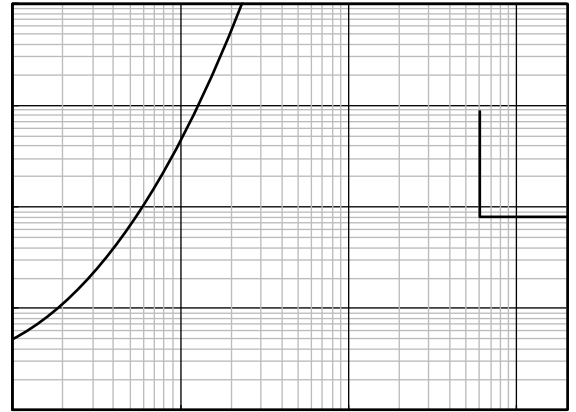


Figure 14. Safe Operation Area

Test Circuits & Waveforms

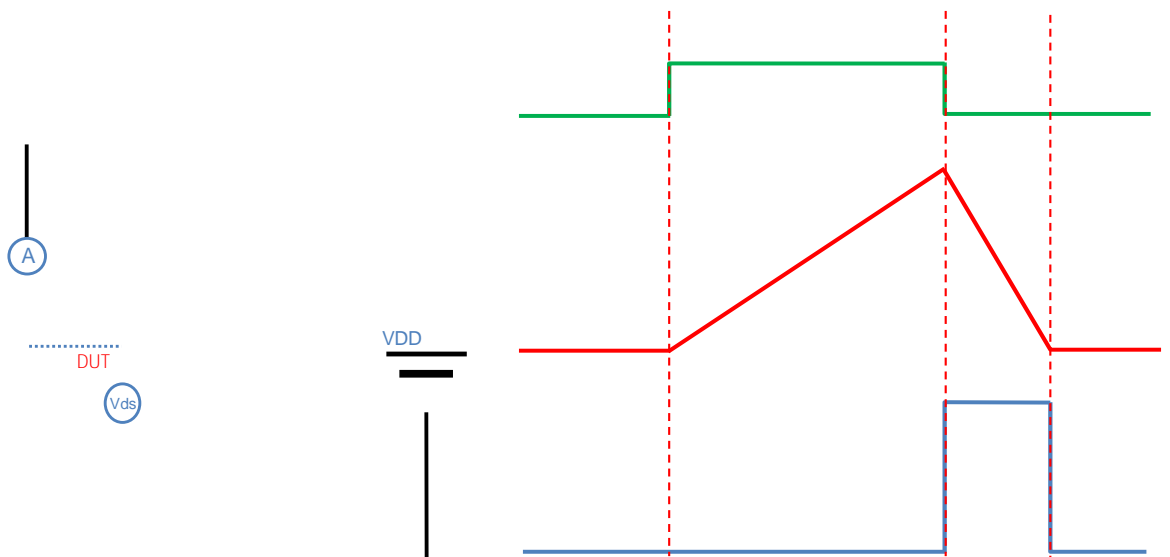
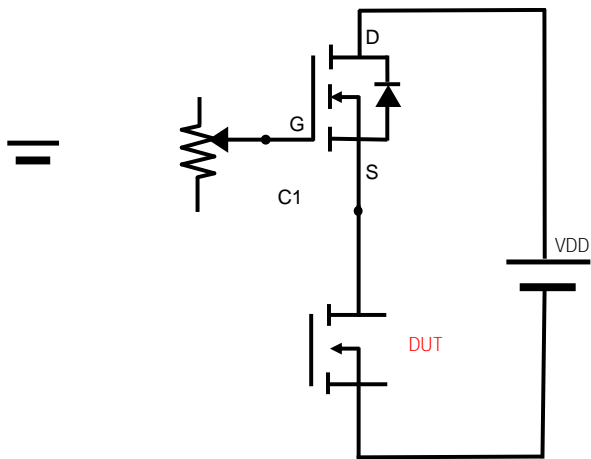
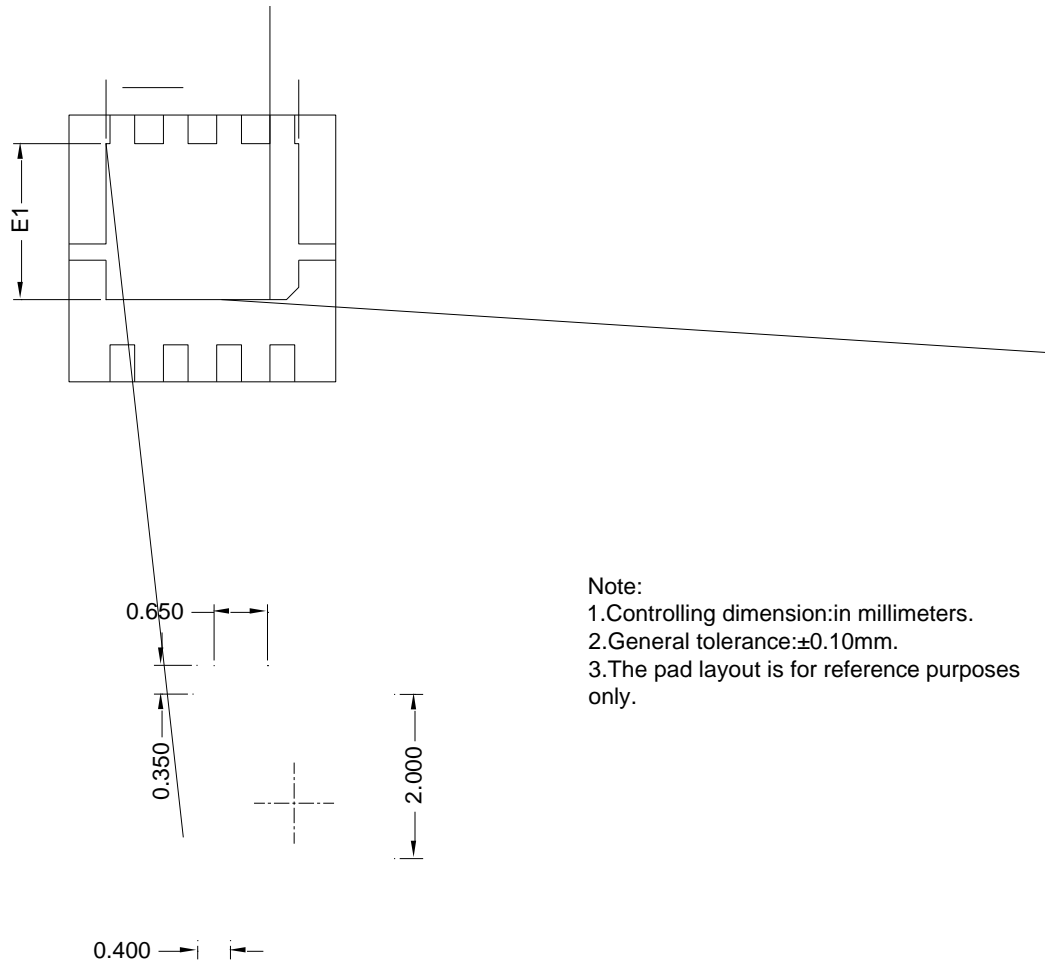


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform





DFN3333-8L-A-0.8MM Package information



Suggested Solder Pad Layout
Top View



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